Contents

Preface xiii

PART A. TENTH AMERICAN CONFERENCE ON CRYSTAL GROWTH

SECTION I. THERMAL AND KINETIC MODELING OF MELT GROWTH

Parallel adaptive 3D finite element analysis of CZ melt flows
D. Givoli, J.E. Flaherty and M.S. Shephard 1
Numerical simulations of transport processes during Czochralski growth of semiconductor compounds
Q. Xiao 7
Modelling of crystal growth process in heat exchanger method
J.H. Wang, D.H. Kim and J.-S. Huh 13
Visualization of convection in Czochralski melts using salts under realistic thermal boundary conditions
U. Krzyminski and A.G. Ostrogorsky 19
Orientation dependence of the distribution coefficient obtained from a spin-1 Ising model
K.M. Beatty and K.A. Jackson 28
Solute distribution during rapid solidification into an undercooled melt
G.-X. Wang, V. Prasad and E.F. Matthys 35

SECTION II. PHASE FIELD MODELING AND DENDRITIC GROWTH

Adaptive phase-field computations of dendritic crystal growth
R.J. Braun and B.T. Murray 41
Phase-field simulation of three-dimensional dendrites: is microscopic solvability theory correct?
A. Karma and W.-J. Rappel, 54
Primary dendrite spacing as a function of directional solidification parameters in an Al–Si–Cu alloy
C.T. Rios and R. Caram 65
Lamellar spacing selection in a directionally solidified Sn–Se eutectic alloy
M.R. Aguiar and R. Caram 70
Growth behavior of NH_4Cl–H_2O mixtures
K.A. Blackmore, K.M. Beatty, M.J. Hui and K.A. Jackson 76

SECTION III. CRYSTAL GROWTH IN MICROGRAVITY

Use of microgravity to interpret dendritic growth kinetics at small supercoolings
L.A. Tennenhouse, M.B. Koss, J.C. LaCombe and M.E. Glicksman 82
The microgravity environment: its prediction, measurement, and importance to materials processing
B.P. Matisak, A.X. Zhao, R. Narayanan and A.L. Fripp 90
Melt growth of striation and etch pit free GaSb under microgravity
T. Nishinaga, P. Ge, C. Huo, J. He and T. Nakamura 96
Effect of residual accelerations during microgravity directional solidification of mercury cadmium telluride on the USMP-2 mission
D.C. Gillies, S.L. Lehoczky, F.R. Szofran, D.A. Watring, H.A. Alexander and G.A. Jerman 101
Comparison of OARE accelerometer data with dopant distribution in Se-Doped GaAs crystals grown during USML-1
M.E. Moskowitz, J.M. Bly and D.H. Matthiesen 108
Void formation in gallium arsenide crystals grown in microgravity
M.L. Kaforey, J.M. Bly and D.H. Matthiesen 112
Physical vapor transport of mercurous chloride crystals: design of a microgravity experiment
W.M.B. Duval, N.B. Singh and M.E. Glicksman 120

Vapor deposited organic thin film in microgravity
M.I. Zugrav, F.C. Wessling, W.E. Carswell, T.M. Leslie, C. Watson and C.A. Lundquist 130
Performance testing of a vertical Bridgman furnace using experiments and numerical modeling
W.R. Rosch, A.L. Fripp, W.J. Debnam and T.K. Pendergrass 139
Model-based calibration of NASA CGF furnace
L. Vujisic and S. Motakef 153
Inertial effects in magnetically stabilized thermocapillary convections during floating-zone semiconductor crystal growth in space
T.E. Morthland and J.S. Walker 159

SECTION IV. Si AND Ge

A model for oxygen precipitation in Czochralski silicon during crystal growth
S. Kobayashi 163
Impurity transients in multiple crystal growth from a single crucible for EFG silicon octagons
J. Cao, M. Prince and J.P. Kalejs 170
Impurity segregation in LPE growth of silicon from Cu–Al solutions
T.H. Wang and T.F. Ciszek 176
Czochralski growth of Si- and Ge-rich SiGe single crystals
N.V. Abrosimov, S.N. Rossolenko, W. Thieme, A. Gerhardt and W. Schröder 182
Silicon–germanium bulk alloy growth by liquid encapsulated zone melting
D. Bliss, B. Demczyk, A. Anselmo and J. Bailey 187
Determination of the Peltier coefficient of germanium in a vertical Bridgman-Stockbarger furnace
M.E.K. Wiegel and D.H. Matthiesen 194
The effect of sample preparation on spreading resistance measurements of doped semiconductors
A. Trujillo and D.H. Matthiesen 202

SECTION V. III–V SEMICONDUCTORS

Active control of the electrical properties of semi-insulating GaAs
W.M. Higgins, R.M. Ware, M.S. Tiernan, K.J. O'Hearn and D.J. Carlson 208
Electrical conduction through compound semiconductor wafer bonded interfaces
D.A. Vanderwater, F.A. Kish, M.J. Peansky and S.J. Rosner 213
Interface shape and growth rate analysis of Se/GaAs bulk crystals grown in the NASA crystal growth furnace (CGF)
J.M. Bly, M.L. Kaforey, D.H. Matthiesen and A. Chait 220
Gravity effect on dissolution and growth of GaSb by liquid-phase epitaxy
H. Kanai, M. Kimura, S. Dost, A. Tanaka and T. Sukegawa 226
Characterization of structural defects in MLEK grown InP single crystals using synchrotron white beam X-ray topography
H. Chung, W. Si, M. Dudley, A. Anselmo, D.F. Bliss, A. Maniatty, H. Zhang and V. Prasad 230
In-situ visualization of off-stoichiometric equilibrium crystal growth within indium antimonide: antimony-rich composition
T.A. Campbell and J.N. Koster 238
Impurity distribution in InSb single crystals
Meng-jun Hui, K. Beatty, K. Blackmore and K. Jackson 245
Cellular structure in LEC ternary $Ga_{1-x}In_xAs$ crystals
D. Reid, B. Lent, T. Bryskiewicz, P. Singer, E. Mortimer and W.A. Bonner 250

SECTION VI. COMPOUND AND II–VI SEMICONDUCTORS

Growth and characterization of p-type $Cd_{1-x}Zn_xTe$ ($x = 0.2, 0.3, 0.4$)
N.N. Kolesnikov, A.A. Kolchin, D.L. Alov, Yu.N. Ivanov, A.A. Chernov, M. Schieber, H. Hermon, R.B. James, M.S. Goorsky, H. Yoon, J. Toney, B. Brunett and T.E. Schlesinger 256

Optimal thermal conditions for growth of $Cd_{1-x}Mn_xTe$(:Cr) (:Cl) (:In) (:V) single crystals using the Bridgman–Stockbarger configuration
K. Grasza, S.B. Trivedi, Z. Yu, S.W. Kutcher and G.A. Brost 263
Seeded growth of HgZnTe by directional solidification using an initial composition profile simulating a "diffusion-boundary" layer
Y.-G. Sha, C.-H. Su, H.A. Alexander, S.L. Lehoczky and J.-C. Wang 267
Single crystal growth of large, crack-free $CdGeAs_2$
P.G. Schunemann and T.M. Pollak 272
Synthesis and growth of $HgGa_2S_4$ crystals
P.G. Schunemann and T.M. Pollak 278
Chalcopyrite Cu(In,Ga)Se_2 and defect-chalcopyrite $Cu(In,Ga)_3Se_5$ materials in photovoltaic P–N junctions
M.A. Contreras and R. Noufi 283
Preparation of ZnSe substrates by PVD and selective etching
T. Sukegawa, F. Kadotsuji, T. Tsujimoto, M. Kaji, M. Kimura and A. Tanaka 289

SECTION VII. OXIDES

Trends in the growth of stoichiometric single crystals
S. Erdei and F.W. Ainger 293
Structural aspects in crystal growth of anhydrous borates
N.I. Leonyuk 301
Melt supercooling behavior and crystal growth of $Ba(B_{1-x}M_x)_2O_4$ (M: Al or Ga)
H. Kimura, T. Numazawa and M. Sato 308
Observation of the growth mechanisms of lithium niobate single crystal during a LHPG process
J.-C. Chen, Y.-C. Lee and C. Hu 313
Growth conditions and composition of $SrPrGaO_4$ single crystals
R. Uecker, P. Reiche, S. Ganschow, P.-M. Wilde, D.-C. Uecker, H. Worzala and D. Schultze 320
Microwave dielectric property measurements of $LaSrGaO_4$ single crystals having possible HTSC substrate applications
S. Erdei, M. McNeal, S.J. Jang, L.E. Cross, A.S. Bhalla, F.W. Ainger, A. Dabkowski and H.A. Dabkowska 324
UV absorption edge position for characterization of YVO_4 crystals grown by Czochralski and TSSG techniques
S. Erdei, B.M. Jin and F.W. Ainger 328
Czochralski growth and characterization of $(Lu_{1-x}Gd_x)_2SiO_5$ single crystals for scintillators
G.B. Loutts, A.I. Zagumennyi, S.V. Lavrishchev, Yu.D. Zavartsev and P.A. Studenikin 331
Progress in the crystal growth of Ce : colquiriites
V.K. Castillo and G.J. Quarles 337
Crystal growth and superconductivity of $TlBa_2Ca_3Cu_4O_{11-\delta}$
L. Zhang, J.Z. Liu, I.M. Littlewood and R.N. Shelton 342
Twin domains in nickel-oxide type crystals
V.S. Mandel 346

SECTION VIII. PROTEIN AND SOLUTION CRYSTAL GROWTH

Protein versus conventional crystals: creation of defects
A.A. Chernov 354
Momentum and mass transfer in supersaturated solutions and crystal growth from solution
A.F. Izmailov and A.S. Myerson 362
Relationship between diffusivity and viscosity for supersaturated electrolyte solutions
A.S. Myerson and A.F. Izmailov 369
Interfacial structure analysis for the prediction of morphology of crystals and implications for the design of tailor-made additives
X.Y. Liu 380
Intergrowth of calcium phosphates: an interfacial energy approach
Y. Liu, W. Wu, G. Sethuraman and G.H. Nancollas 386
Crystal growth and optical properties of 4-aminobenzophenone crystals for NLO applications
R.B. Lal, H.W. Zhang, W.S. Wang, M.D. Aggarwal, H.W.H. Lee and B.G. Penn 393

SECTION IX. FILM GROWTH: OXIDES, ORGANICS AND METALS

Comparison of heteroepitaxial $YBa_2Cu_3O_{7-\delta}$ and TiO_2 thin film growth
A. Roshko, F.J.B. Stork, D.A. Rudman, D.J. Aldrich and P.A. Morris Hotsenpiller 398
Simple model for the nucleation of (0 0 1) and (1 0 0) oriented grains in YBCO films
F.M. Granozio and U.S. di Uccio 409
Growth of epitaxial Sr_2RuO_4 films and $YBa_2Cu_3O_{7-\delta}/Sr_2RuO_4$ heterostructures
S. Madhavan, J.A. Mitchell, T. Nemoto, S. Wozniak, Y. Liu, D.G. Schlom, A. Dabkowski and H.A. Dabkowska 417
Growth morphologies of heteroepitaxial rutile films on sapphire substrates
P.A. Morris Hotsenpiller, A. Roshko, J.B. Lowekamp and G.S. Rohrer 424
Growth of beta barium borate (β-BaB_2O_4) thin films for nonlinear optical applications
H.B. Liao, R.F. Xiao, P. Yu and G.K.L. Wong 434
Composition of MBE-grown iron oxide films
F.C. Voogt, T. Hibma, P. Smulders and L. Niesen 440
Heteroepitaxial growth of α-Fe_2O_3, γ-Fe_2O_3 and Fe_3O_4 thin films by oxygen-plasma-assisted molecular beam epitaxy
Y. Gao and S.A. Chambers 446
CMR films structure as a function of growth and processing
M.E. Hawley, C.D. Adams, P.N. Arendt, E.L. Brosha, F.H. Garzon, R.J. Houlton, M.F. Hundley, R.H. Heffner, Q.X. Jia, J. Neumeier and X.D. Wu 455
MOCVD of Pb-based ferroelectric oxide thin films
M. Shimizu, H. Fujisawa and T. Shiosaki 464
Epitaxial lead titanate grown by MBE
C.D. Theis and D.G. Schlom 473
Application of exhaustive lattice match searches to the selection of epitaxial substrates for protein crystal growth
P.J. Shlichta 480
Epitaxy versus oriented heterogeneous nucleation of organic crystals on ionic substrates
K.R. Sarma, P.J. Shlichta, W.R. Wilcox and R.A. Lefever 487
Effect of structure on the mechanical properties of Ta and Ta(N) thin films prepared by reactive DC magnetron sputtering
R. Saha and J.A. Barnard 495
Stress and microstructure of nanocrystalline FeXN (X = Ta, Si, and Al) thin films
M.K. Minor and J.A. Barnard 501
A computational model for calculation of misfit stress distribution in multilayer crystals
Z. Qin and S. Dost 506

PART B. NINTH INTERNATIONAL CONFERENCE ON VAPOR GROWTH AND EPITAXY

SECTION X. VAPOR GROWTH KINETICS

Surface kinetics of metalorganic vapor-phase epitaxy: surface diffusion, nucleus formation, sticking at steps
M. Kasu and N. Kobayashi 513
Morphological instabilities, segregation, and reconstruction at $GaAs/Al_xGa_{1-x}As$ interfaces: a more realistic picture of the normal and inverted interface
K.H. Ploog 522
Computer simulation of surface growth
R.-F. Xiao 531
Arsenic pressure dependence of pure two-face inter-surface diffusion between (0 0 1) and (1 1 1)B in molecular beam epitaxy of GaAs
A. Yamashiki, X.Q. Shen and T. Nishinaga 539

SECTION XI. IN-SITU PROCESS MONITORING FOR VAPOR GROWTH PROCESSES

Origin of surface reflectance spectrum during epitaxy
N. Kobayashi, Y. Kobayashi and K. Uwai 544
In situ detection of misfit dislocations by light scattering
K.L. Kavanagh, R.S. Goldman, C. Lavoie, B. Leduc, T. Pinnington, T. Tiedje, D. Klug and J. Tse 550

Surface-related optical anisotropy of GaInP, InP, and GaP
J.S. Luo, J.F. Geisz, J.M. Olson and M.-C. Wu 558
In situ pre-growth calibration using reflectance as a control strategy for MOCVD fabrication of device structures
W.G. Breiland, H.Q. Hou, H.C. Chui and B.E. Hammons 564

SECTION XII. VAPOR DEPOSITION OF III–V SEMICONDUTORS

Adatom concentration on GaAs(0 0 1) during annealing
M.D. Johnson, K.T. Leung, A. Birch and B.G. Orr 572
MOCVD growth of high efficiency current-matched AlGaAs/Si tandem solar cell
T. Soga, K. Baskar, T. Kato, T. Jimbo and M. Umeno 579
Effect of growth parameters on step structure and ordering in GaInP
Y.S. Chun, S.H. Lee, I.H. Ho and G.B. Stringfellow 585
The growth of mid-infrared lasers and $AlAs_xSb_{1-x}$ by MOCVD
R.M. Biefeld, A.A. Allerman and S.R. Kurtz 593
MOCVD growth of InGa(Al)As/InAlAs multilayer heterostructures for long wavelength DBRs
S.W. Choi, K.S. Suh, J.W. Lee 599
MOCVD growth and optical characterization of strain–induced quantum dots with InP island stressors
M.C. Hanna, Z.H. Lu, A.F. Cahill, M.J. Heben and A.J. Nozik 605
Comparison of chlorocarbons as an additive during MOVPE for flat burying growth of InP
T. Takeuchi and T. Tanahashi 611
Selective area growth of AlGaAs on GaAs by PSE/MBE
G. Bacchin, K. Tsunoda and T. Nishinaga 616
Spatially resolved photoluminescence of laterally overgrown InP on InP-coated Si substrates
S. Naritsuka and T. Nishinaga 622
Effect of growth temperature on epitaxial lateral overgrowth of GaAs on Si substrate
Y.S. Chang, S. Naritsuka and T. Nishinaga 630
Crystallization process of amorphous GaAs buffer layers for the heteroepitaxial growth of GaAs on Si(0 0 1) substrates
Y. Matsunaga, S. Naritsuka and T. Nishinaga 635

SECTION XIII. VAPOR DEPOSITION OF HIGH BANDGAP MATERIALS

A comparative study of OMVPE-grown InN heteroepitaxial layers on GaAs(1 1 1)B and α-Al_2O_3(0 0 0 1) substrates
A. Yamamoto, Y. Yamauchi, M. Ohkubo and A. Hashimoto 641
Structural properties of GaN grown by MOVPE turbodisc mass-production reactor
C.A. Tran, R. Karlicek, M. Schurman, T. Salagaj, R. Cassidy, I. Ferguson, A.G. Thompson, R.A. Stall and C.-Y. Hwang 647
3C–SiC growth by alternate supply of SiH_2Cl_2 and C_2H_2
K. Yagi and H. Nagasawa 653
Thin film growth of silicon carbide from methyl-trichloro-silane by RF plasma-enhanced CVD
T. Kaneko, N. Miyakawa, H. Sone and M. Iijima 658
Improvement in the growth rate of cubic silicon carbide bulk single crystals grown by the sublimation method
H.N. Jayatirtha, M.G. Spencer, C. Taylor and W. Greg 662
SiC-bulk growth by physical-vapor transport and its global modelling
D. Hofmann, R. Eckstein, M. Kölbl, Y. Makarov, St.G. Müller, E. Schmitt, A. Winnacker, R. Rupp, R. Stein, J. Völkl 669

SECTION XIV. VAPOR DEPOSITION OF Si, Ge AND Si/Ge ALLOYS

The stability of ordered structures in SiGe films examined by strain-energy calculations
T. Araki, N. Fujimura and T. Ito 675
Structural and electrical properties of silicon epitaxial layers grown by LPE and CVD on identical polycrystalline substrates
G. Wagner, H. Wawra, W. Dorsch, M. Albrecht, R. Krome, H.P. Strunk, S. Riedel, H.J. Möller and W. Appel 680
Initial growth characteristics of germanium on silicon in LPCVD using germane gas
S. Kobayashi, M. Sakuraba, T. Matsuura, J. Murota and N. Mikoshiba 686

SECTION XV. VAPOR DEPOSITION OF II–VI MATERIALS AND CHALCOGENIDES

Effect of Ce doping on the growth of ZnO thin films
Y. Morinaga, K. Sakuragi, N. Fujimura and T. Ito 691
Growth of twin-free CdTe single crystals in a semi-closed vapour phase system
M. Laasch, T. Kunz, C. Eiche, M. Fiederle, W. Joerger, G. Kloess and K.W. Benz 696
The reactivity of dimethylcadmium on GaAs(1 0 0) and CdTe(1 0 0)
K. Yong, J.J. Reinoso, A.J. Gellman and P.J. Sides 708
Kinetic limitations on incorporation of Zn in $Cd_{1-x}Zn_xTe$
J.J. Reinoso, E.I. Ko and P.J. Sides 713
Low supersaturation nucleation and "contactless" growth of photorefractive ZnTe crystals
K. Grasza, S.B. Trivedi, Z. Yu, S.W. Kutcher, W. Palosz and G.A. Brost 719
Structural properties of ZnS_ySe_{1-y}/ZnSe/GaAs(0 0 1) heterostructures grown by photoassisted metalorganic vapor phase epitaxy
X.G. Zhang, S. Kalisetty, J. Robinson, G. Zhao, D.W. Parent, J.E. Ayers and F.C. Jain 726
Seeded physical vapor transport of cadmium–zinc telluride crystals: growth and characterization
W. Palosz, M.A. George, E.E. Collins, K.-T. Chen, Y. Zhang, Z. Hu and A. Burger 733
Partial pressure monitoring in cadmium telluride vapour growth
J. Carles, J.T. Mullins and A.W. Brinkman 740
Electrical fluctuations in HgCdTe introduced during quenching after annealing
H. Ebe and K. Yamamoto 746
Investigation of the interfacial quality and the influence of different substrates in ZnSe homoepitaxy
H. Wenisch, T. Behr, J. Kreissl, K. Schüll, D. Siche, H. Hartmann and D. Hommel 751
Near-band-edge photoluminescence of MOVPE-grown undoped and nitrogen-doped ZnSe
A.L. Gurskii, I.P. Marko, V.N. Yuvchenko, G.P. Yablonskii, H. Hamadeh, W. Taudt, J. Söllner, H. Kalisch and M. Heuken 757
Optical-pumped lasing of doped ZnSe epilayers grown by MOVPE
G.P. Yablonskii, A.L. Gurskii, E.V. Lucenko, I.P. Marko, H. Hamadeh, W. Taudt, J. Söllner, H. Kalisch and M. Heuken 763
The MBE temperature window for $Cd_{1-x}Zn_xTe$ ($0 \leqslant x \leqslant 1$) compounds grown on 2°-off oriented GaAs(1 0 0) substrates
M.A. Herman, A.V. Kozhukhov and J.T. Sadowski 768
Characterization of ternary substrate materials using triple axis X-ray diffraction
H. Yoon, S.E. Lindo and M.S. Goorsky 775
Chemical vapor transport and optical, magnetic and structural characterization of platelete-type $Mn_xHo_{1-x}InSe_4$ single crystals
A. Khan, J. Diaz, V. Sagredo, R. Vargas 783

SECTION XVI. OXIDES

The initial stage of $BaTiO_3$ epitaxial films on etched and annealed $SrTiO_3$ substrates
T. Yoshimura, N. Fujimura and T. Ito 790
Formation of $YMnO_3$ films directly on Si substrate
N. Aoki, N. Fujimura, T. Yoshimura and T. Ito 796
Kinetics of evaporation of barium THD precursors used for organometallic chemical vapor deposition (OMCVD) thin films
V. Burtman, M. Schieber, S. Yitzchaik and Y. Yaroslavsky 801
Misfit problems in epitaxy of high-T_c superconductors
I. Utke, C. Klemenz, H.J. Scheel, M. Sasaura and S. Miyazawa 806
High-temperature X-ray measurements of gallates and cuprates
I. Utke, C. Klemenz, H.J. Scheel and P. Nüesch 813

SECTION XVII. FILM GROWTH

Growth of large fullerene C_{60} crystals and highly oriented thin films by physical vapor transport
R.-F. Xiao 821

Preparation of pristine and Ba-doped C_{60} films by hot-wall epitaxy
H. Sitter, D. Stifter and T.N. Manh 828
Experimental and theoretical investigations of low-pressure CVD of Cu using CuI as precursor
A. Möller, R. Kall, V. Till, G. Wortberg and G. Adomeit 837
Growth and characterization of bismuth and antimony thin films
A. Martínez, R. Collazo, A.R. Berríos and G.O. Ducoudray 845
The initial stages of Ag/Ag(1 0 0) homoepitaxy: scanning tunneling microscopy experiments and Monte Carlo simulations
C.-M. Zhang, M.C. Bartelt, J.-M. Wen, C.J. Jenks, J.W. Evans and P.A. Thiel 851

Author index 858

Subject index 866